Supplementary Materials:

Super Color Purity Green Quantum Dot Light-Emitting Diodes by Using CdSe/CdS Nanoplatelets

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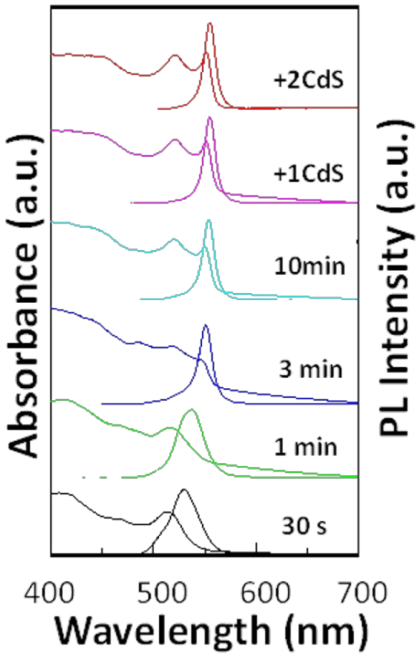

Figure S1. UV−vis and PL spectra of CdSe nanoplatelets with different reaction time

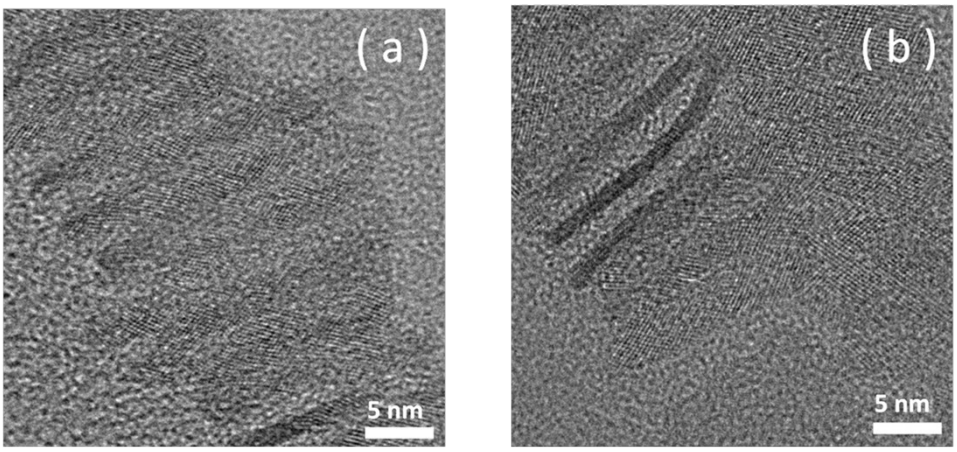

Figure S2. HRTEM images of CdSe and CdSe/CdS nanoplatelets

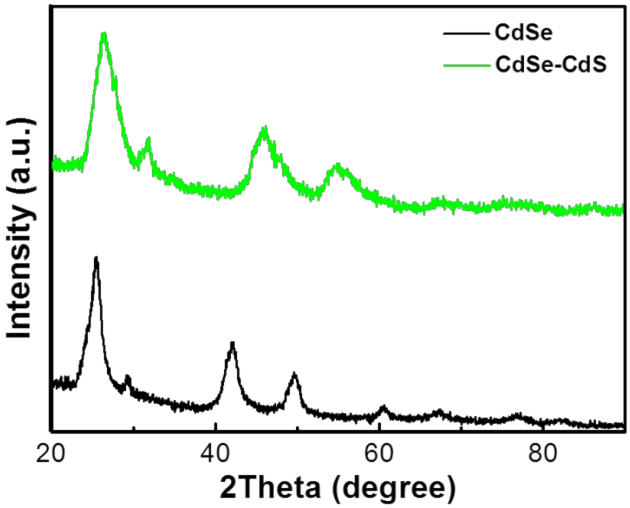

Figure S3. XRD pattern of CdSe and CdSe/CdS nanoplatelets

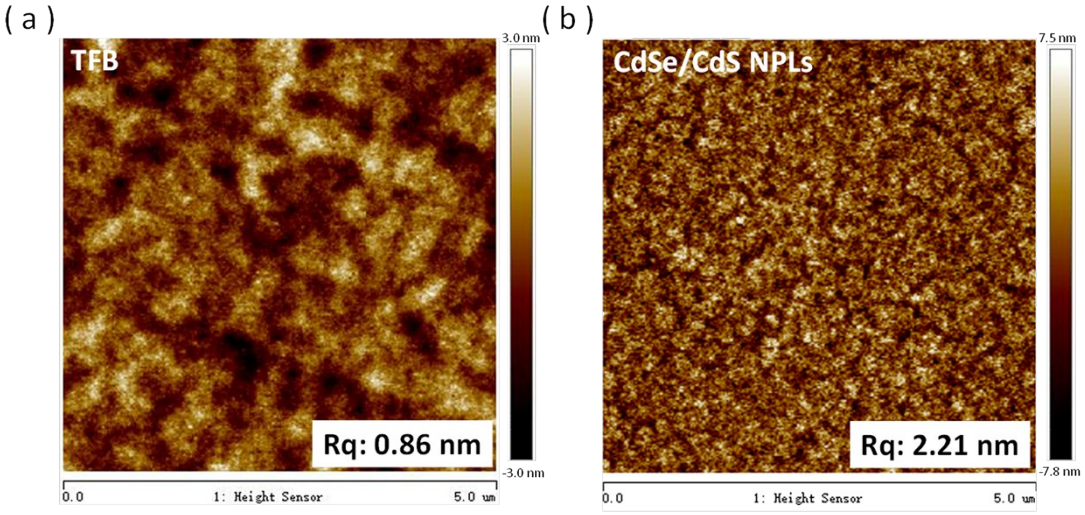

Figure S4. AFM characteristics of roughness (Rq) of (a) TFB and (b) CdSe/CdS nanoplatelets layers.

ITO/PEDOT: PSS (30 nm)/TFB (40 nm)/QDs (x nm)/ZnO (30 nm)/Al (100 nm)

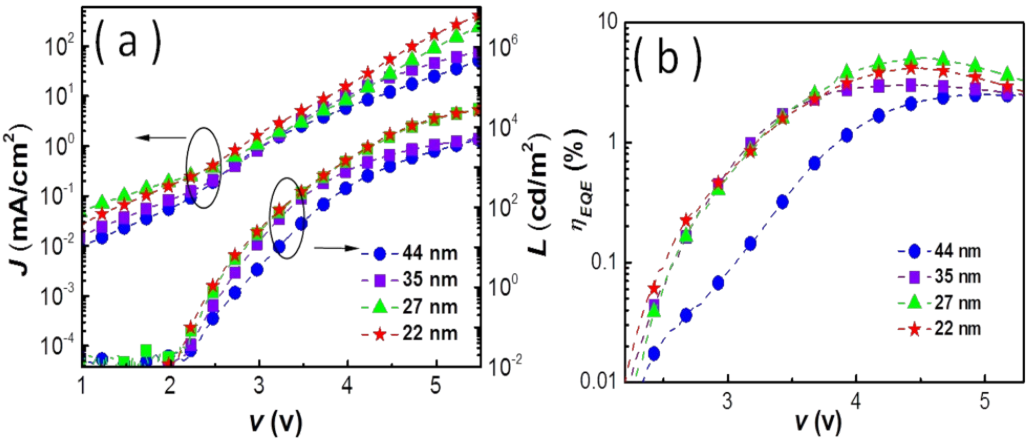

Figure S5. (a) Current density-voltage-luminance (*J-V-L*) characteristics of QLED based on NPL by varying the QDs layer thickness. (b) External quantum efficiency (η_{EQE}) of these devices as a function of the driving voltage.

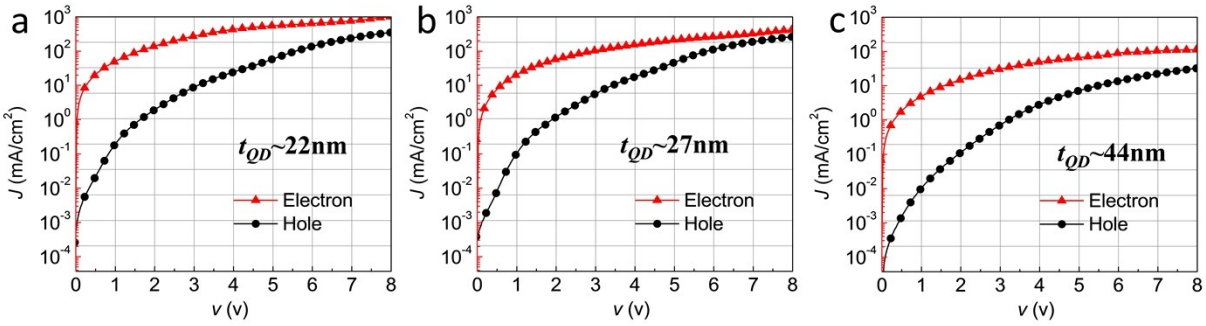

Figure S6. Current-density-voltage (J-V) characteristics of electron- and hole- only devices based on ~22nm (a), 27nm (b), and 44nm (c) thick QDs.

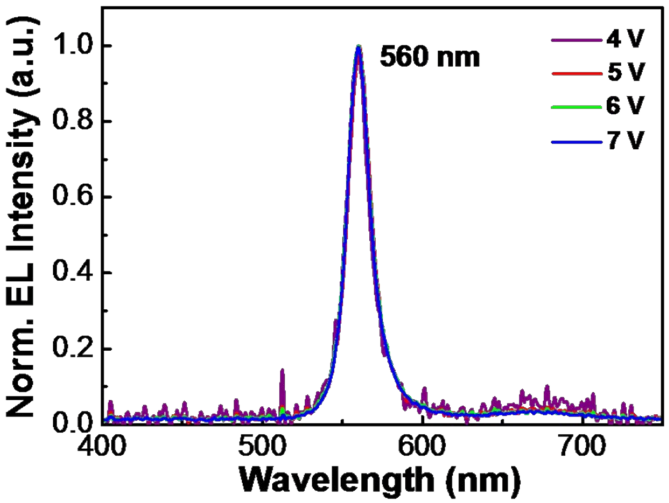

Figure S7. Normalize EL spectra of QLED with increasing bias voltage.